BUJ302AD

NPN power transistor

28 April 2018 Product data sheet

1. General description

High voltage, high speed planar passivated NPN power switching transistor in a SOT428 (DPAK) surface mountable plastic package.

2. Features and benefits

- Fast switching
- Low thermal resistance
- Surface mountable package
- Very high voltage capability
- Very low switching and conduction losses

3. Applications

- DC-to-DC converters
- High frequency electronic lighting ballasts
- Inverters
- Motor control systems

4. Quick reference data

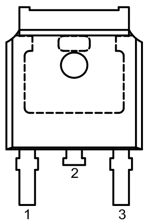
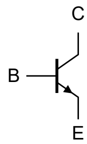
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CM}	peak collector current	Fig. 1; Fig. 2; Fig. 3		-	-	8	A
P_{tot}	total power dissipation	$T_{mb} \leq$ 25 °C; Fig. 4		-	-	80	W
V_{CESM}	collector-emitter peak voltage	V_{BE} = 0 V		-	-	1050	V
Static characteristics							
h_{FE}	DC current gain	I_C = 0.1 A; V_{CE} = 5 V; T_{mb} = 25 °C; Fig. 11	[1]	48	66	100	
		I_C = 0.8 A; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12	[1]	25	42	50	

[1] Pulse test: pulse duration ≤ 300 µs, duty cycle ≤ 2 %

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 **DPAK (SOT428)**	 sym123
2	C	collector[1]		
3	E	emitter		
mb	C	mounting base; connected to collector		

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

6. Ordering information

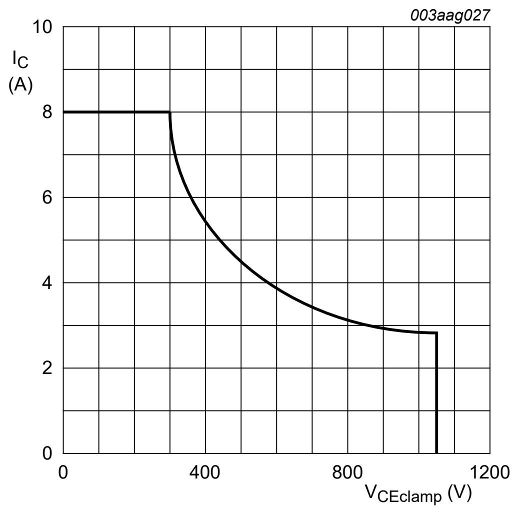
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUJ302AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

7. Limiting values

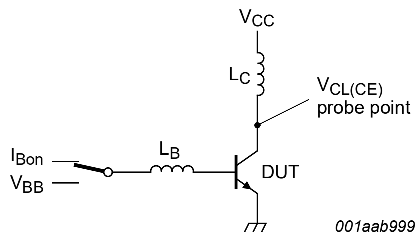
Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	V_{BE} = 0 V		-	1050	V
V_{CEO}	collector-emitter voltage	I_B = 0 A		-	400	V
V_{EBO}	emitter-base voltage	I_C = 0 A; I_E = 2 A; t_p < 10 ms		-	24	V
I_C	collector current	Fig. 1; Fig. 2; Fig. 3		-	4	A
I_{CM}	peak collector current			-	8	A
I_B	base current			-	2	A
I_{BM}	peak base current			-	4	A
P_{tot}	total power dissipation	T_{mb} ≤ 25 °C; Fig. 4		-	80	W
T_{stg}	storage temperature			-65	150	°C
T_j	junction temperature			-	150	°C



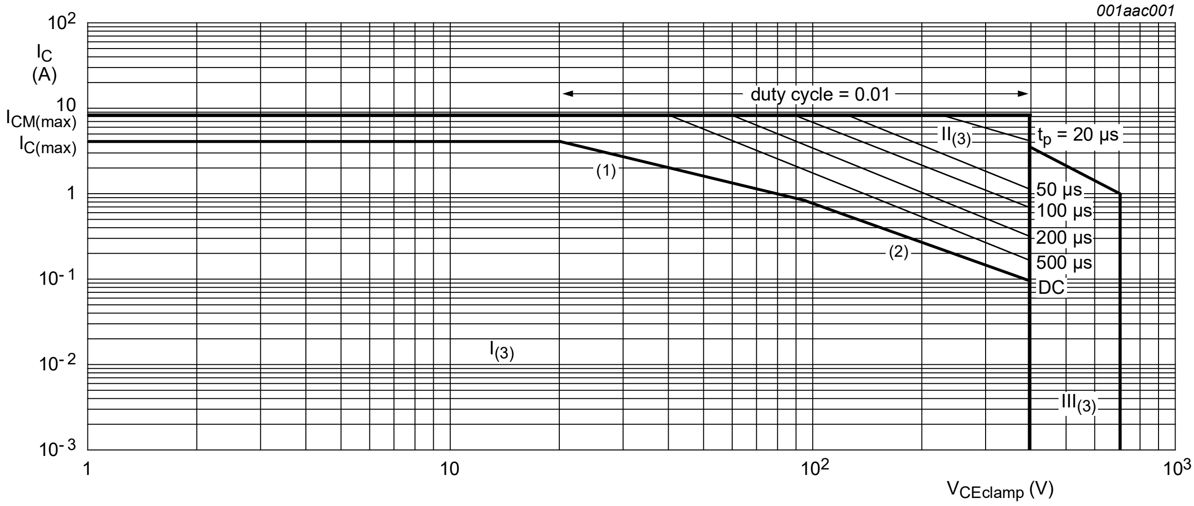
$T_j \leq T_{j(max)}$ °C

Fig. 1. Reverse bias safe operating area



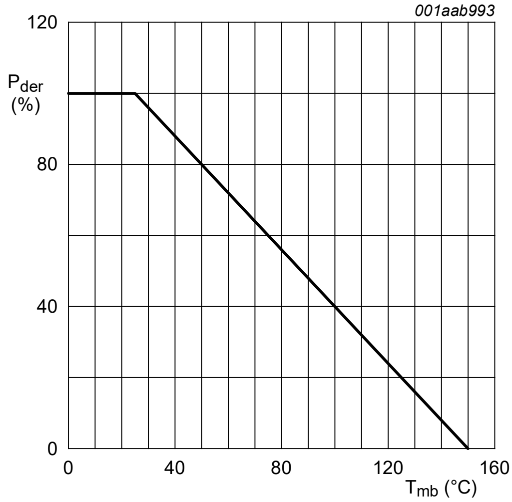
$V_{CL(CE)} \leq 1000\ V; V_{CC} = 150\ V; V_{BB} = -5\ V;$
$L_B = 1\ \mu H; L_C = 200\ \mu H$

Fig. 2. Test circuit for reverse bias safe operating area



1)Ptot maximum and Ptot peak maximum lines
2)Second breakdown limits
3) I = Region of permissable DC operation
II = Extension for repetitive pulse operation
III = Extension during turn-on in single transistor converters
provided that RBE ≤ 100 Ω and tp ≤ 0.6 μs

Fig. 3. Forward bias safe operating area for Tmb ≤ 25 °C



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig. 4. Normalized total power dissipation as a function of mounting base temperature

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint		-	75	-	K/W

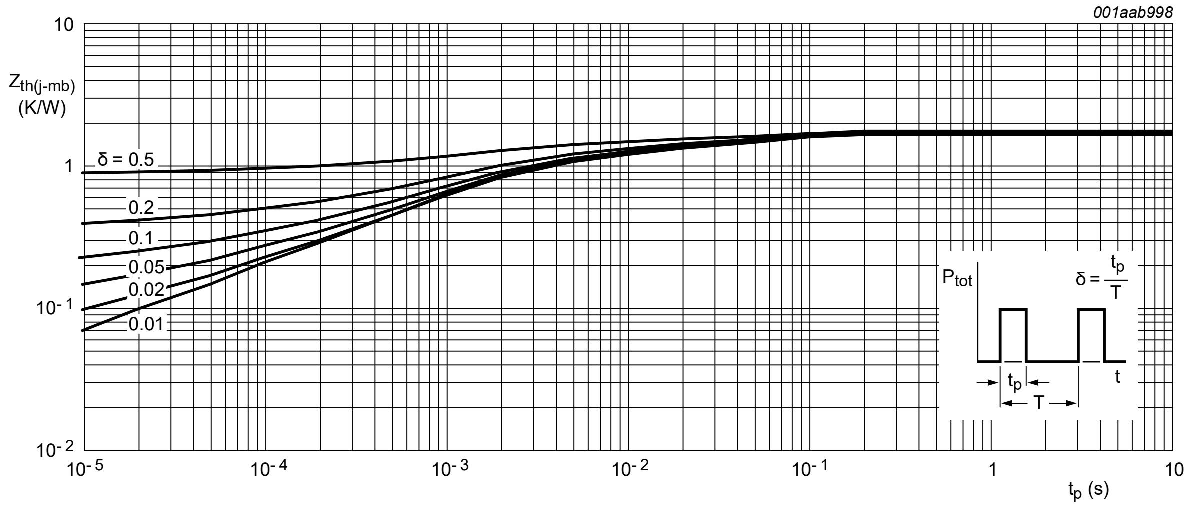


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{CES}	collector-emitter cut-off current (base shorted)	V_{BE} = 0 V; V_{CE} = 1050 V		-	0.2	10	µA
I_{CEO}	collector-emitter cut-off current (base open)	V_{CE} = 400 V; I_B = 0 A; T_{mb} = 25 °C		-	10	250	mA
$V_{(BR)EBO}$	emitter-base breakdown voltage (collector open)	I_B = 1 mA; I_C = 0 A; T_{mb} = 25 °C		15	19	-	V
V_{CEOsus}	collector-emitter sustaining voltage (base open)	I_B = 0 A; I_C = 10 mA; L_C = 25 mH; T_{mb} = 25 °C; Fig. 6; Fig. 7	[1]	400	470	-	V
V_{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 0.2 A; T_{mb} = 25 °C; Fig. 8; Fig. 9	[1]	-	0.15	0.5	V
		I_C = 3.5 A; I_B = 1 A; T_{mb} = 25 °C; Fig. 8; Fig. 9	[1]	-	0.6	1.5	V
V_{BEsat}	base-emitter saturation voltage	I_C = 3.5 A; I_B = 1 A; T_{mb} = 25 °C; Fig. 10	[1]	-	1.1	1.5	V
h_{FE}	DC current gain	I_C = 0.1 A; V_{CE} = 5 V; T_{mb} = 25 °C; Fig. 11	[1]	48	66	100	
		I_C = 0.8 A; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12	[1]	25	42	50	
Dynamic characteristics							
t_s	storage time	I_C = 2.5 A; I_{Bon} = 0.5 A; I_{Boff} = -0.5 A; R_L = 60 Ω; V_{BB} = -5 V; T_{mb} = 25 °C; resistive load; t_p = 300 µs; Fig. 13; Fig. 14		-	-	3.5	µs
t_f	fall time			-	-	500	ns

[1] Pulse test: pulse duration ≤ 300 µs, duty cycle ≤ 2 %

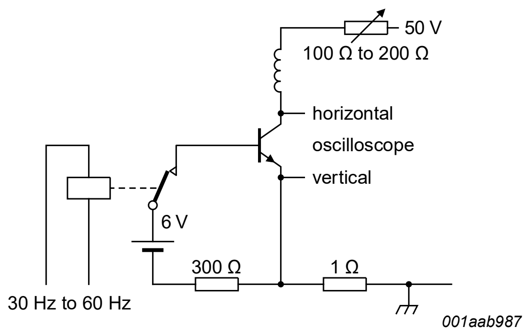


Fig. 6. Test circuit for collector-emitter sustaining voltage

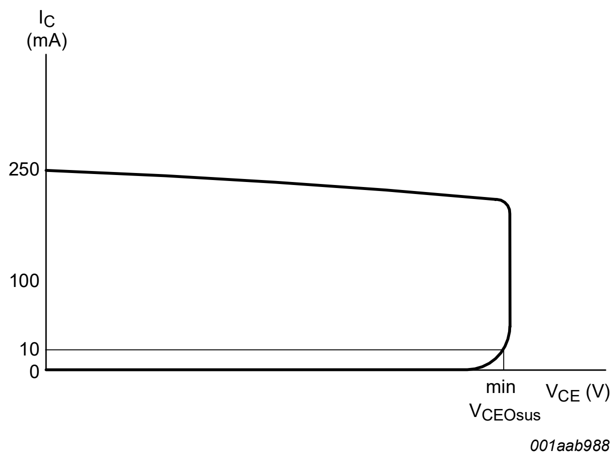
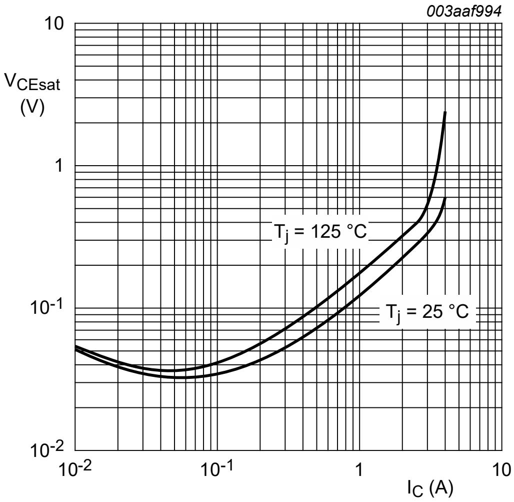


Fig. 7. Oscilloscope display for collector-emitter sustaining voltage test waveform



$I_C/I_B = 3$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

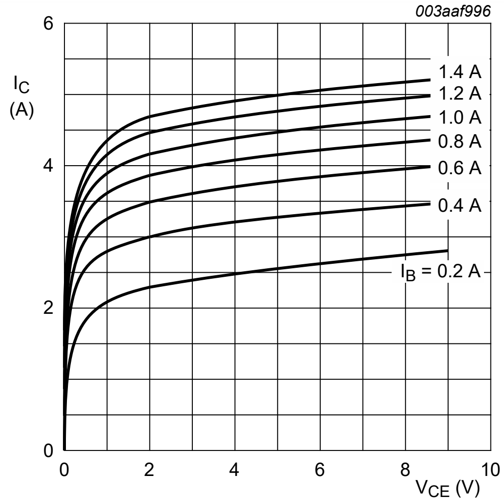
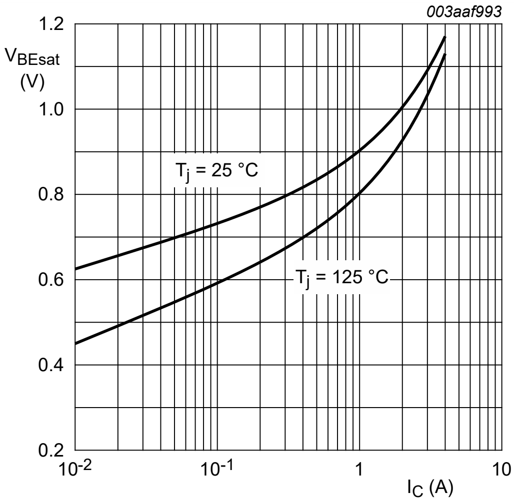


Fig. 9. Collector current as a function of collector-emitter voltage; typical values



$I_C/I_B = 3$

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

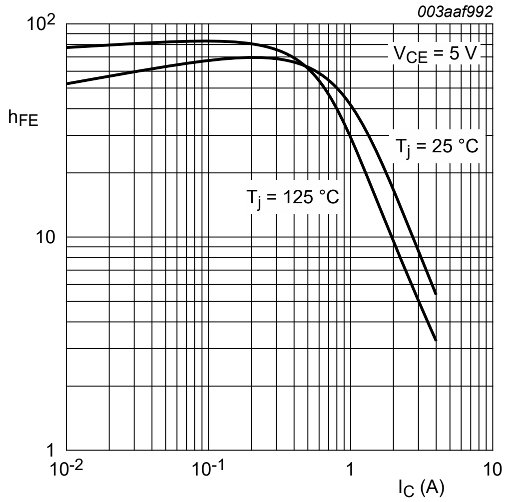


Fig. 11. DC current gain as a function of collector current; typical values

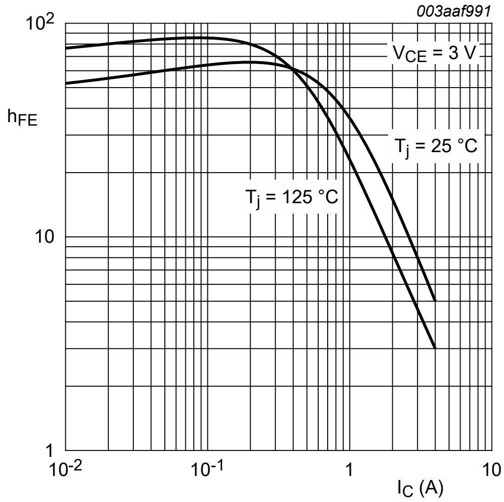
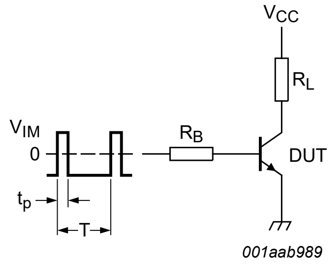


Fig. 12. DC current gain as a function of collector current; typical values



$V_{IM} = -6$ to $+8$ V; $V_{CC} = 250$ V; $t_p = 20$ µs; $\delta = \frac{t_p}{T} = 0.01$

R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig. 13. Test circuit for resistive load switching

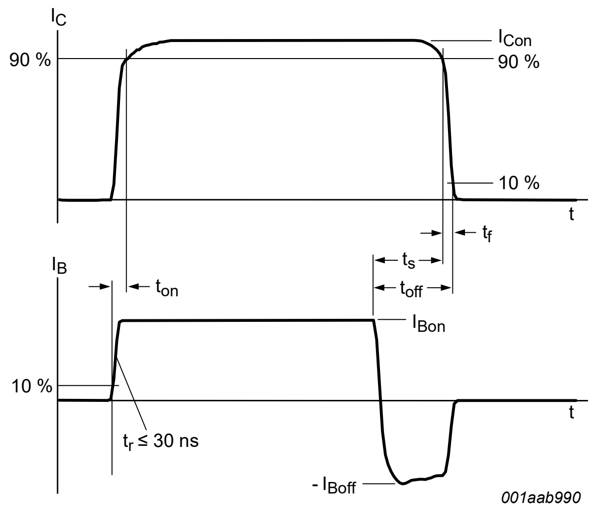
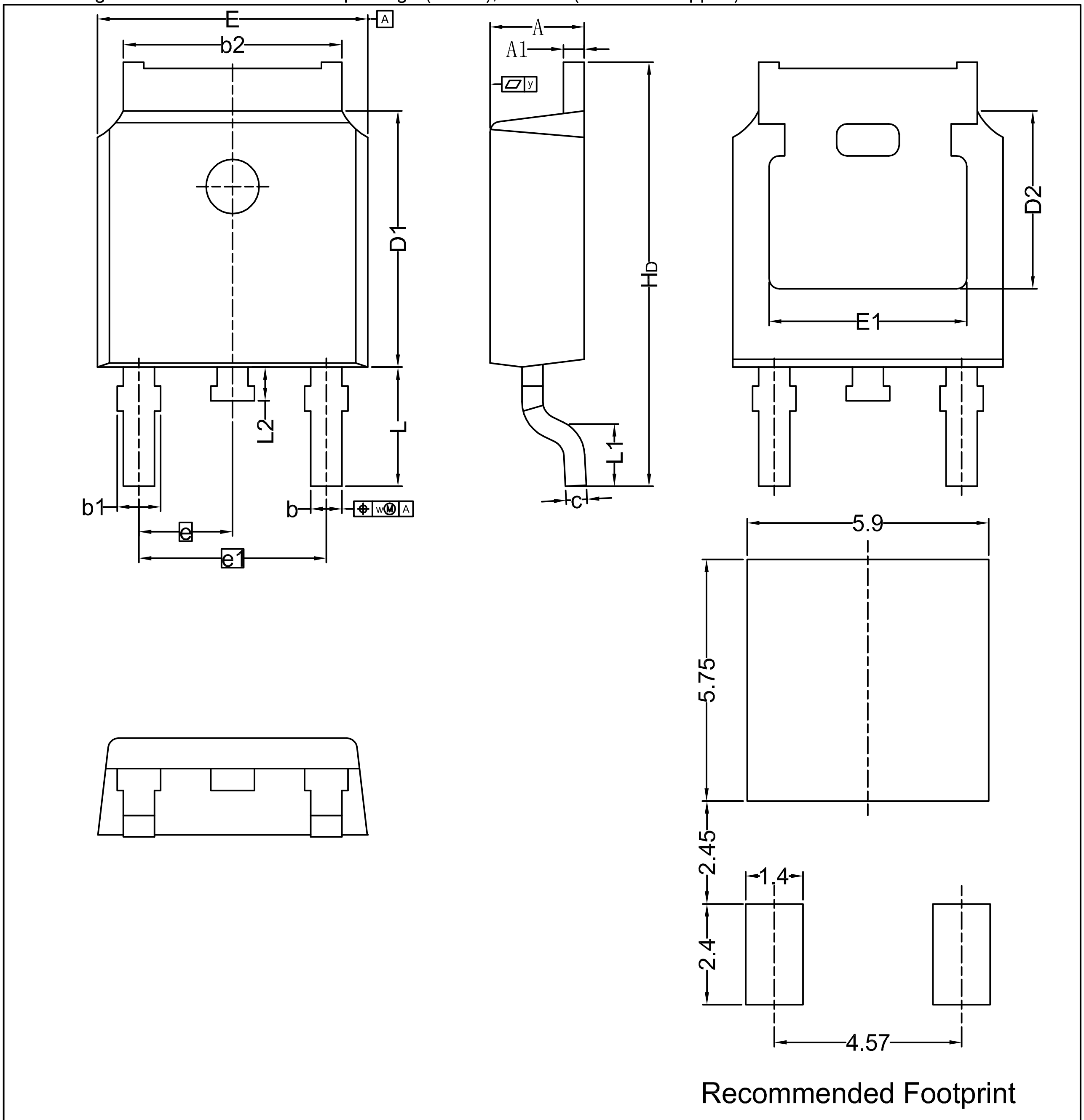


Fig. 14. Switching times waveforms for resistive load

10. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) TO252



Unit		A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H_D	L	L1	L2	w	y
mm	min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45			9.60		0.50	0.50		
	nom											2.285	4.57		2.90 (Ref.)			0.20	
	max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40		---	0.90		0.20

Fig. 15. Package outline DPAK (SOT428)

11. Soldering

Footprint information for reflow soldering of DPAK (SOT428) package **SOT428**

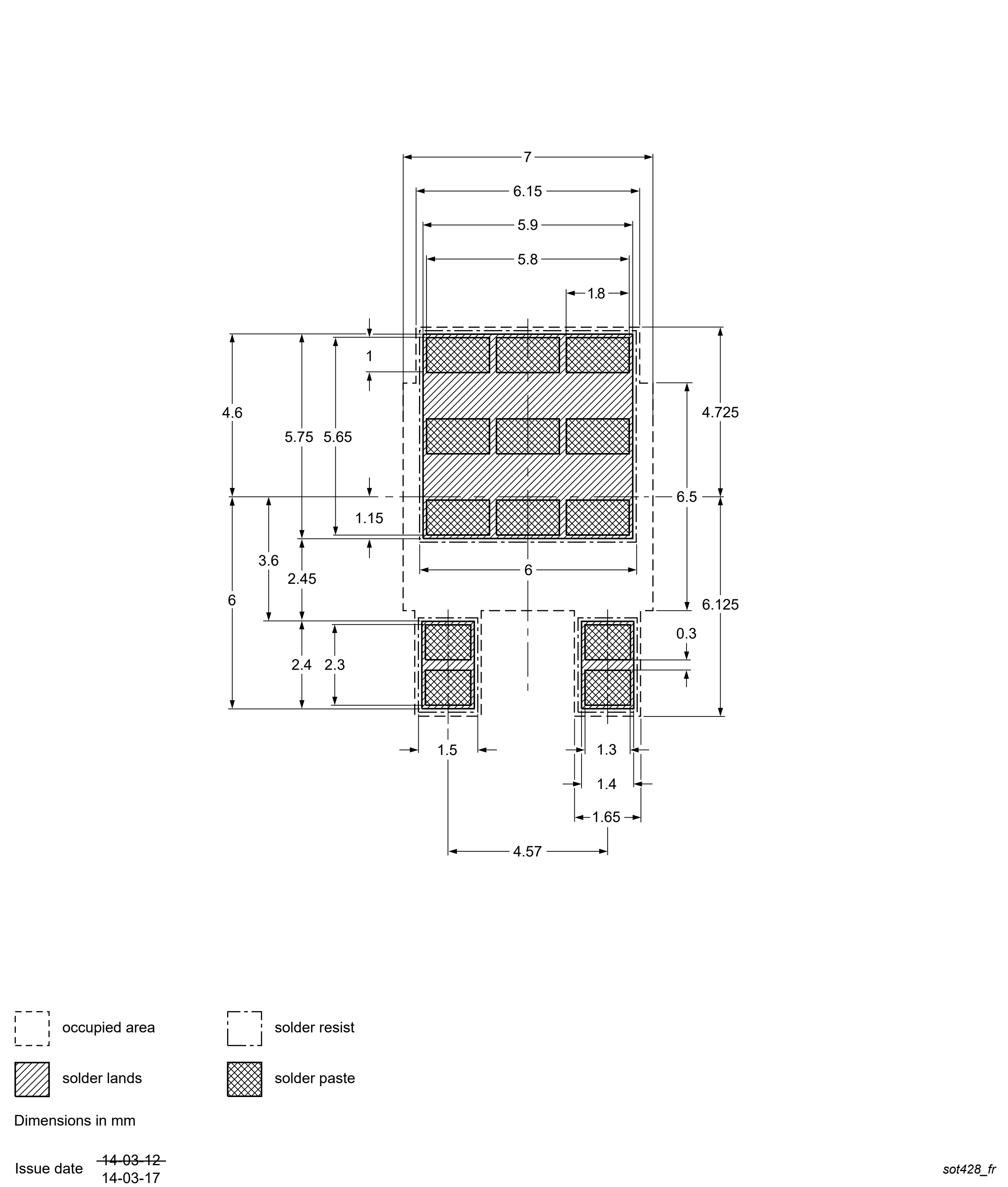


Fig. 16. Wave soldering footprint for DPAK (SOT428)

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Document status [1][2]	Product status [3]	Definition
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